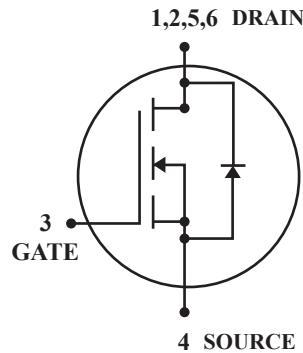


## N-Channel Enhancement Mode Power MOSFET

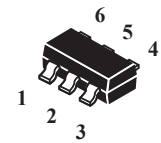
**(Pb)** Lead(Pb)-Free



**DRAIN CURRENT**  
**6.3 AMPERES**  
**DRAIN SOURCE VOLTAGE**  
**20 VOLTAGE**

### Features:

- \*Super High Dense Cell Design For Low  $R_{DS(ON)}$   
 $R_{DS(ON)} < 34m\Omega @ V_{GS}=4.5V$
- \*Rugged and Reliable
- \*Capable of 2.5V Gate Drive
- \*Simple Drive Requirement
- \*SOT-26 Package



**SOT-26**

### Maximum Ratings ( $T_A=25^\circ C$ Unless Otherwise Specified)

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current <sup>3</sup> , $V_{GS}@4.5V$ , $T_A=25^\circ C$ $T_A=70^\circ C$	$I_D$	6.3	A
		5	
Pulsed Drain Current <sup>1,2</sup>	$I_{DM}$	30	
Total Power Dissipation( $T_A=25^\circ C$ )	$P_D$	2	W
Maximum Junction-ambient	$R\theta_{JA}$	62.5	$^\circ C/W$
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ C$

### Device Marking

WTL2602=2602

**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  Unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Static**

Drain-Source Breakdown Voltage $V_{GS}=0, I_D=250\mu\text{A}$	$BV_{DSS}$	20	-	-	V
Gate-Source Threshold Voltage $V_{DS}=V_{GS}, I_D=250\mu\text{A}$	$V_{GS(Th)}$	0.5	-	-	
Gate-Source Leakage current $V_{GS}=\pm 12\text{V}$	$I_{GSS}$	-	-	$\pm 100$	nA
Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ ) $V_{DS}=20\text{V}, V_{GS}=0$	$I_{DSS}$	-	-	1	$\mu\text{A}$
Drain-Source Leakage Current ( $T_j=55^\circ\text{C}$ ) $V_{DS}=16\text{V}, V_{GS}=0$		-	-	10	
Drain-Source On-Resistance $V_{GS}=10\text{V}, I_D=5.5\text{A}$ $V_{GS}=4.5\text{V}, I_D=5.3\text{A}$ $V_{GS}=2.5\text{V}, I_D=2.6\text{A}$ $V_{GS}=1.8\text{V}, I_D=1.0\text{A}$	$R_{DS(on)}$	-	-	30 34 50 90	$\text{m}\Omega$
Forward Transconductance $V_{DS}=5\text{V}, I_D=5.3\text{A}$	gfs	-	13	-	S

**Dynamic**

Input Capacitance $V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1.0\text{MHz}$	$C_{iss}$	-	603	1085	pF
Output Capacitance $V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1.0\text{MHz}$	$C_{oss}$	-	144	-	
Reverse Transfer Capacitance $V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1.0\text{MHz}$	$C_{rss}$	-	111	-	

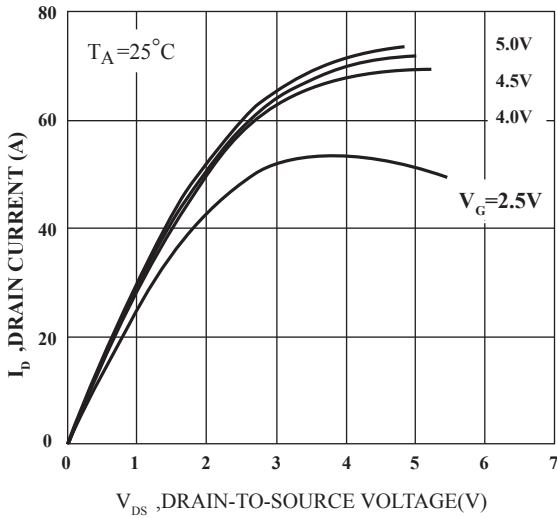
## Switching

Turn-on Delay Time <sup>2</sup> $V_{DS}=15V, V_{GS}=10V, I_D=1A, R_D=15\Omega, R_G=2\Omega$	$t_{d(on)}$	-	6	-	ns
Rise Time $V_{DS}=15V, V_{GS}=10V, I_D=1A, R_D=15\Omega, R_G=2\Omega$	$t_r$	-	14	-	
Turn-off Delay Time $V_{DS}=15V, V_{GS}=10V, I_D=1A, R_D=15\Omega, R_G=2\Omega$	$t_{d(off)}$	-	18.4	-	
Fall Time $V_{DS}=15V, V_{GS}=10V, I_D=1A, R_D=15\Omega, R_G=2\Omega$	$t_f$	-	2.8	-	
Total Gate Charge <sup>2</sup> $V_{DS}=10V, V_{GS}=4.5V, I_D=5.3A$	$Q_g$	-	8.7	16	nC
Gate-Source Charge $V_{DS}=10V, V_{GS}=4.5V, I_D=5.3A$	$Q_{gs}$	-	1.5	-	
Gate-Source Change $V_{DS}=10V, V_{GS}=4.5V, I_D=5.3A$	$Q_{gd}$	-	3.6	-	

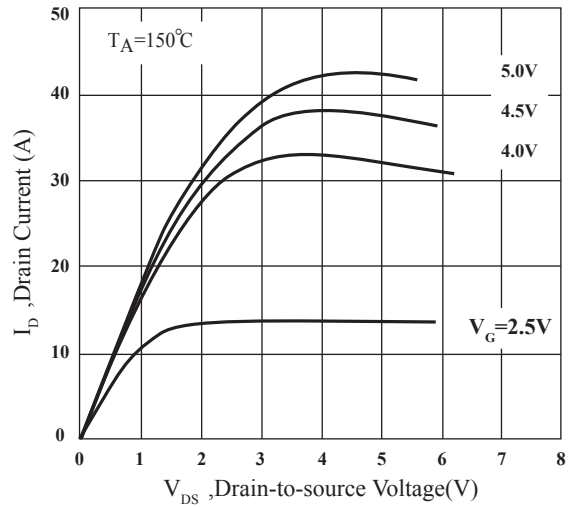
## Source-Drain Diode Characteristics

Forward On Voltage <sup>2</sup> $V_{GS}=0V, I_S=1.2A$	$V_{SD}$	-	-	1.2	V
Reverse Recovery Time $V_{GS}=0V, I_S=5A, di/dt=100A/\mu s$	$T_{rr}$	-	16.8	-	ns
Reverse Recovery Charge $V_{GS}=0V, I_S=5A, di/dt=100A/\mu s$	$Q_{rr}$	-	11	-	nC

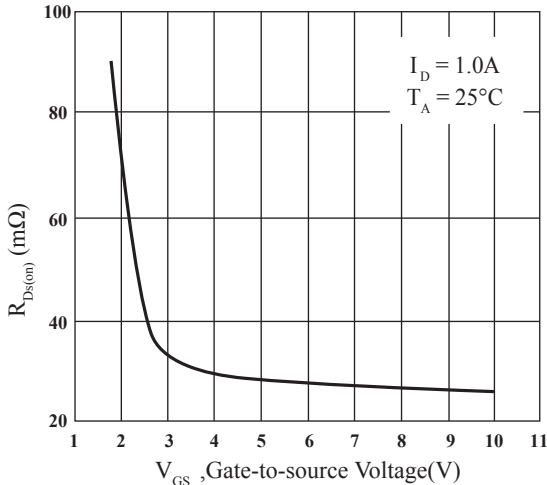
- Note: 1. Pulse width limited by max. junction temperature.  
 2. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .  
 3. Surface mounted on 1 in2 copper pad of FR4 board;  $156^\circ C/W$  when mounted on Min. copper pad.



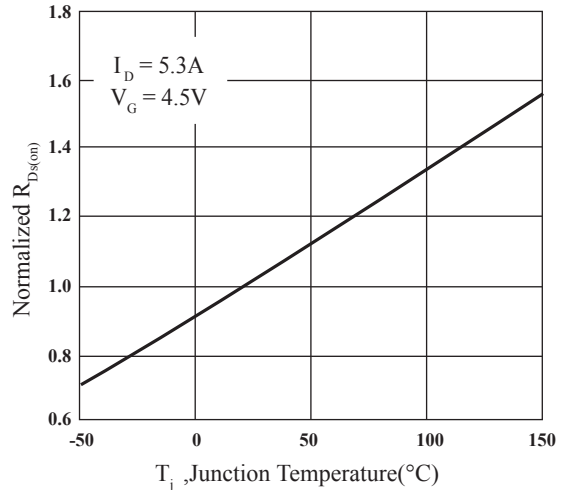
**FIG.1 Typical Output Characteristics**



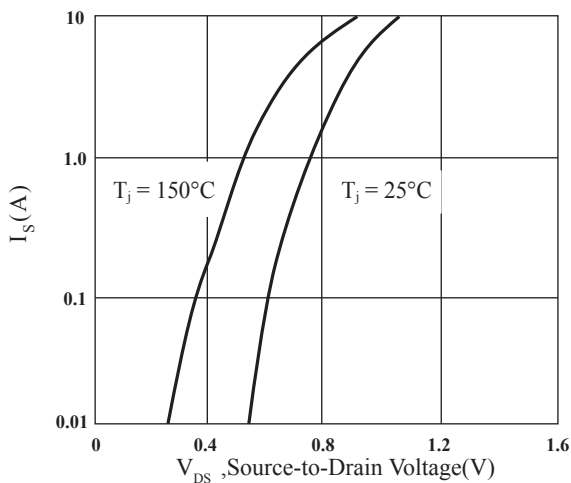
**Fig.2 Typical Output Characteristics**



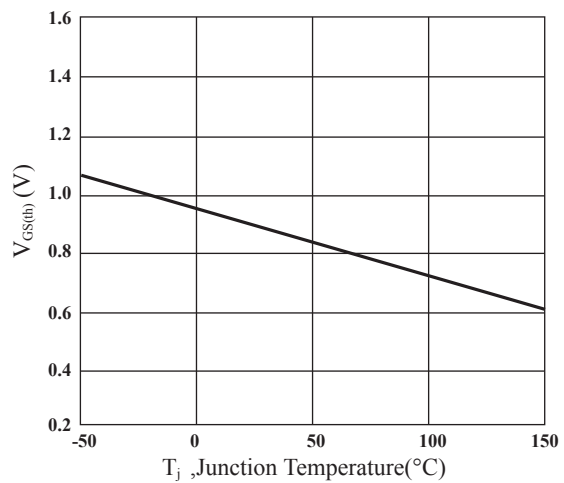
**Fig.3 On-Resistance v.s. Gate Voltage**



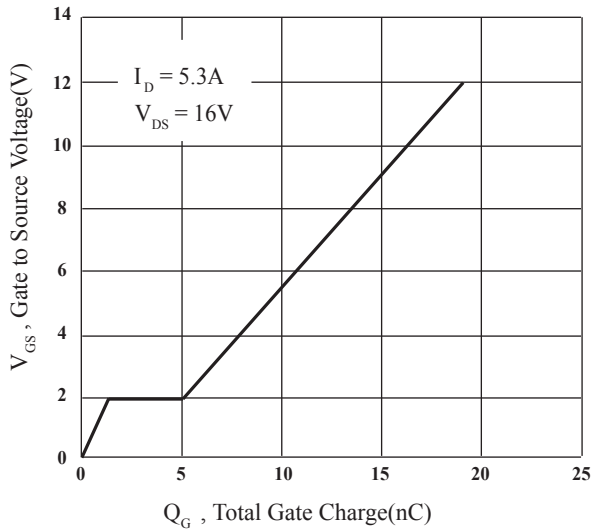
**Fig.4 Normalized OnResistance**



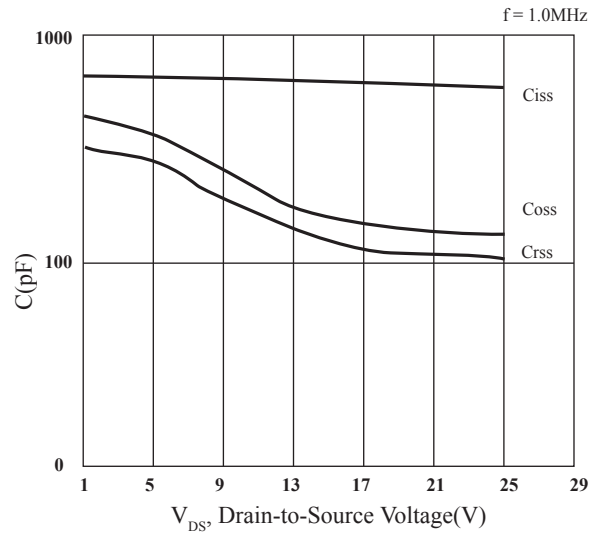
**Fig.5 Forward Characteristics of Reverse Diode**



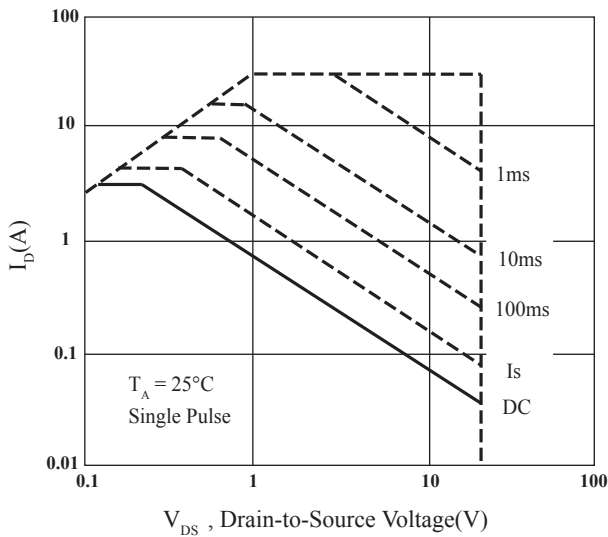
**Fig.6 Gate Threshold Voltage v.s. Junction Temperature**



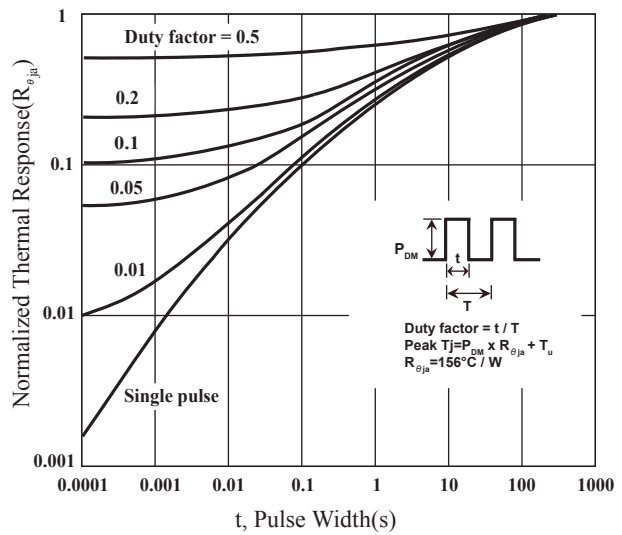
**Fig 7. Gate Charge Characteristics**



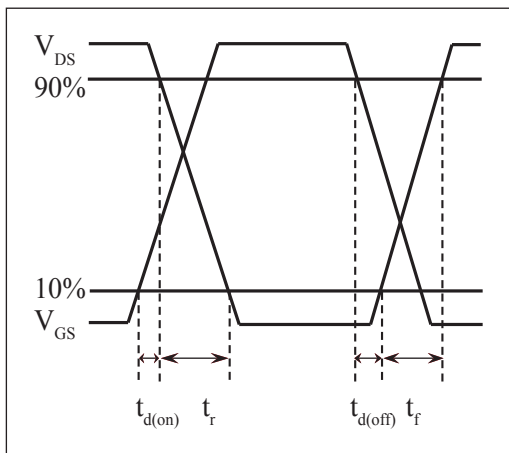
**Fig 8. Typical Capacitance Characteristics**



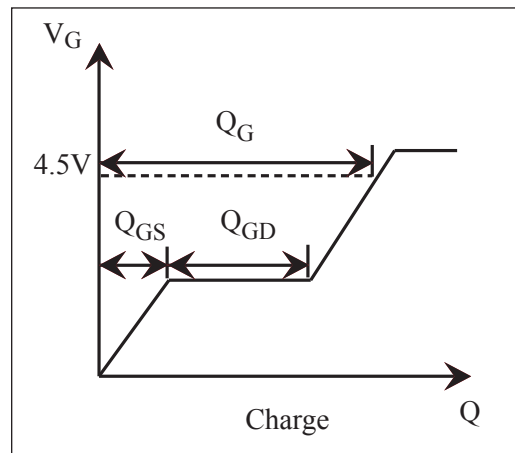
**Fig 9. Maximum Safe Operation Area**



**Fig 10. Effective Transient Thermal Impedance**



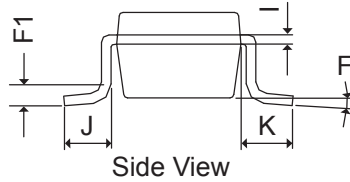
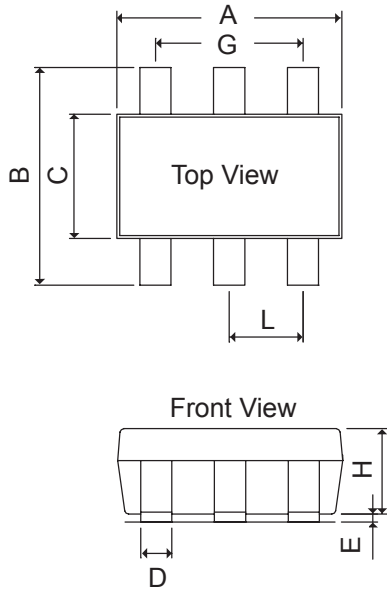
**Fig 11. Switching Time Circuit**



**Fig 12. Gate Charge Waveform**

**SOT-26 Outline Dimension**

Unit:mm



SOT-26		
Dim	Min	Max
A	2.70	3.10
B	2.60	3.00
C	1.40	1.80
D	0.30	0.55
E	0.00	0.10
F	0°	10°
F1	0.08	0.25
G	1.90 REF	
H	1.20 REF	
I	0.12 REF	
J	0.37 REF	
K	0.60 REF	
L	0.95 REF	